



Form 1449 (Modified)		Atty Docket No. LAM1P187/P1216	Application No.: 10/798,456
Information Disclosure Statement By Applicant		Applicant: CHOI et al.	
(Use Several Sheets if Necessary)		Filing Date March 10, 2004	Group 1765

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1.						

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
LTUE	B1.	0050972	05/05/82	EPO	H01L	21/88	X	
LTUE	B2.	0496614	07/29/92	EPO	H01L	21/3105	X	
LTUE	B3.	0553961	08/04/93	EPO	H01L	21/311	X	
LTUE	B4.	0777267	06/04/97	EPO	H01L	21/311	X	
LTUE	B5.	1041614	10/04/00	EPO	H01L	21/306	X	
LTUE	B6.	2000340552	12/08/00	Japan	H01L	21/3065	X	
LTUE	B7.	2001110784	04/20/01	Japan	H01L	21/3065	X	
LTUE	B8.	11-111680	04/23/99	Japan	H01L	21/3065	X	
LTUE	B9.	11-016887	01/22/99	Japan	H01L	21/3065	X	
LTUE	B10.	0889507	01/07/99	EPO	H01L	21/311	X	
LTUE	B11.	0305268	03/01/89	EPO	H01L	21/306	X	

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
LTUE	C1.	Horiike Y. et al., "High Rate and Highly Selective SiO ₂ Etching Employing Inductively Coupled Plasma and Discussion on Reaction Kinetics", Journal of Vacuum Science and Technology: Part A, American Institute of Physics, New York, US, Vol. 13, no. 3, Part 1, 1 May 1995, pp. 801-809.
LTUE	C2.	Kumar M.J. et al., "Selective Reactive Ion Etching of PECVD Silicon Nitride over Amorphous Silicon in CF ₄ /H ₂ and Nitrogen Containing CF ₄ /H ₂ Plasma Gas Mixtures", Solid State Electronics, Elsevier Science Publishers, Barking, GB, vol. 39, no. 1, 1995, pp. 33-37.
LTUE	C3.	Maeda M. et al., "Low Dielectric Constant Amorphous SiBN Ternary Films Prepared by Plasma-Enhanced Deposition", Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Tokyo, Japan, vol. 26, no. 5, Part 1, 1 May 1987, pp. 660-665.
LTUE	C4.	Norstrom H., "Silicon Surface Damage Caused by Reactive Ion Etching in Fluorocarbon Gas Mixtures Containing Hydrogen", Journal of Vacuum Science and Technology: Part B, American Institute of Physics, New York, US, vol. 9, no. 1, 1991, pp. 34-40.

Examiner /Lynette Umez Eronini/	Date Considered (08/17/2006)
---	--

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	LAM1P187/P1216	10/798,456
	Applicant:	
	CHOI et al.	
	Filing Date	Group
	March 10, 2004	1765

LTUE	C5.	Norstrom H. et al., "RIE of SiO ₂ in Doped and Undoped Fluorocarbon Plasmas", Vacuum, Pergamon Press Ltd., Great Britian, Vol. 32, No. 12, pp. 737-745; 1982.
LTUE	C6.	Standaert, T.E.F.M. et al., "Patterning of Fluorine-, Hydrogen-, and Carbon-Containing SiO ₂ -Like Low Dielectric Constant Materials in High-Density Fluorocarbon Plasmas: Comparison with SiO ₂ ", Journal of Vacuum Science and Technology A 173(3), May/June 1999, pp. 741-748.
LTUE	C7.	International Search Report or the Declaration for PCT/US03/18791 dated 01/16/2004.
LTUE	C8.	Written Opinion dated March 2, 2004 for PCT/US03/18791.

Examiner	Date Considered
/Lynette Umez Eronini/	(08/17/2006)

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.